

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Darlington power transistor)

2SD1140

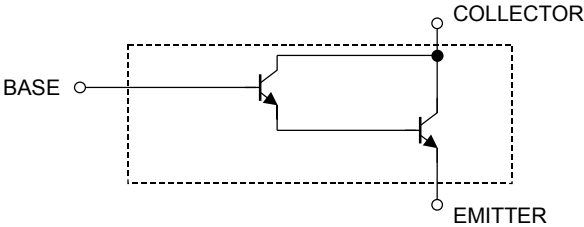
Micro Motor Drive, Hammer Drive Applications
Switching Applications
Power Amplifier Applications

- High DC current gain: $h_{FE} = 4000$ (min) ($V_{CE} = 2\text{ V}$, $I_C = 150\text{ mA}$)
- Low saturation voltage: $V_{CE(sat)} = 1.5\text{ V}$ (max) ($I_C = 1\text{ A}$, $I_B = 1\text{ mA}$)

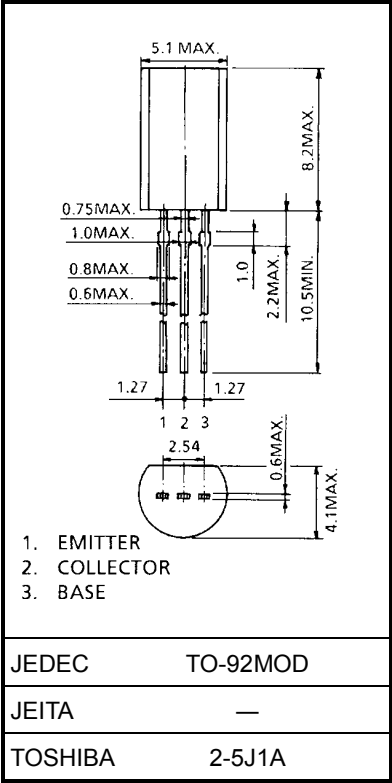
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	10	V
Collector current	I_C	1.5	A
Base current	I_B	50	mA
Collector power dissipation	P_C	900	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

Equivalent Circuit

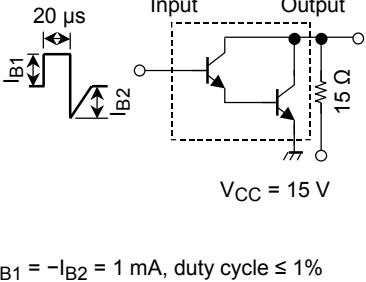


Unit: mm

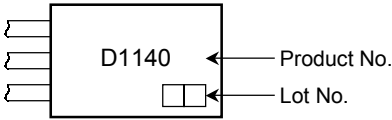


Weight: 0.36 g (typ.)

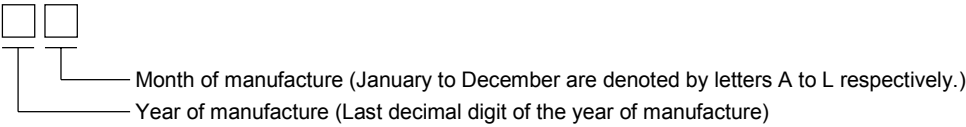
Electrical Characteristics (Ta = 25°C)

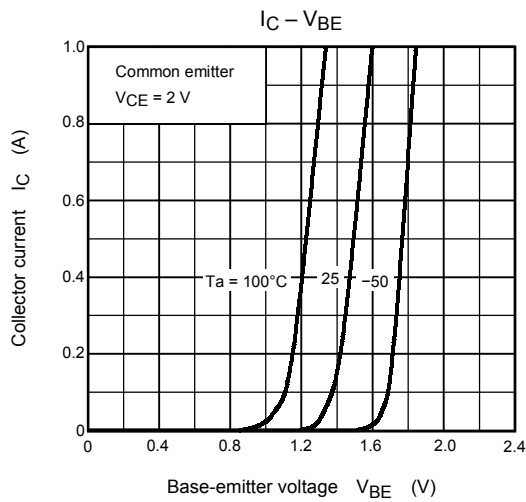
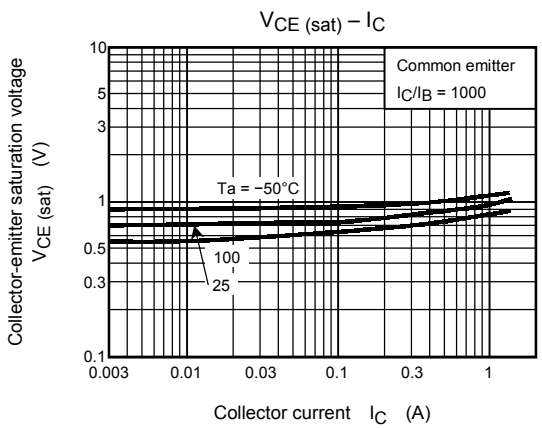
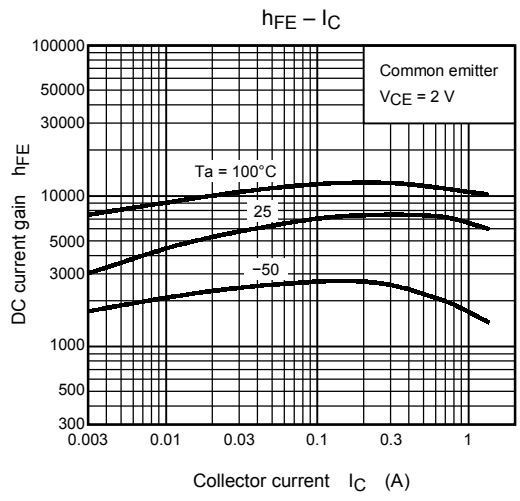
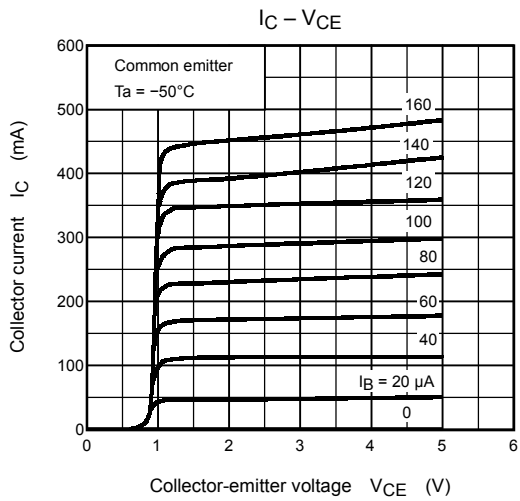
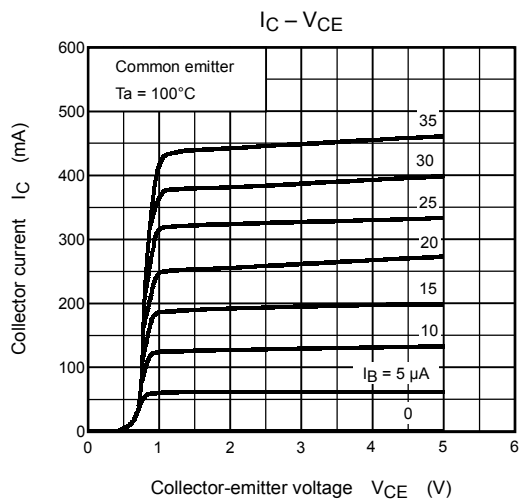
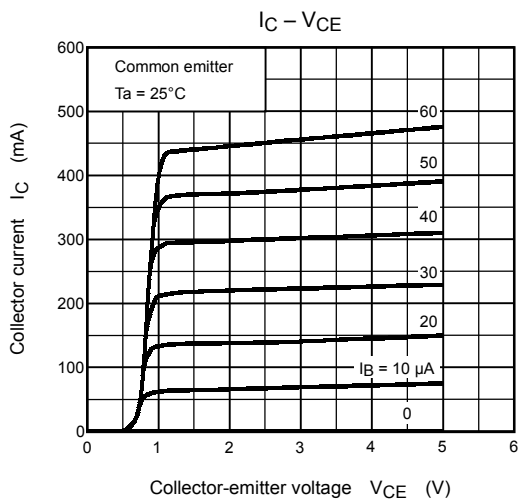
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		ICBO	V _{CB} = 30 V, I _E = 0	—	—	10	μA
Emitter cut-off current		IEBO	V _{EB} = 10 V, I _C = 0	—	—	10	μA
Collector-emitter breakdown voltage		V _(BR) CEO	I _C = 10 mA, I _B = 0	30	—	—	V
DC current gain		h _{FE}	V _{CE} = 2 V, I _C = 150 mA	4000	—	—	
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 1 A, I _B = 1 mA	—		1.5	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = 1 A, I _B = 1 mA	—		2.2	V
Switching time	Turn-on time	t _{on}	 I _{B1} = -I _{B2} = 1 mA, duty cycle ≤ 1%	—	0.2	—	μs
	Storage time	t _{stg}		—	0.6	—	
	Fall time	t _f		—	0.3	—	

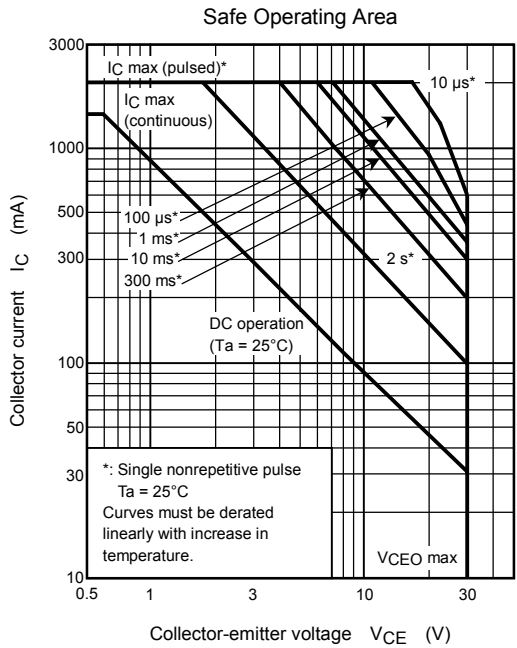
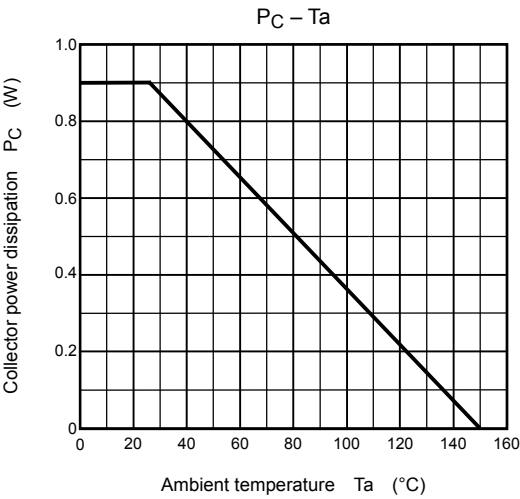
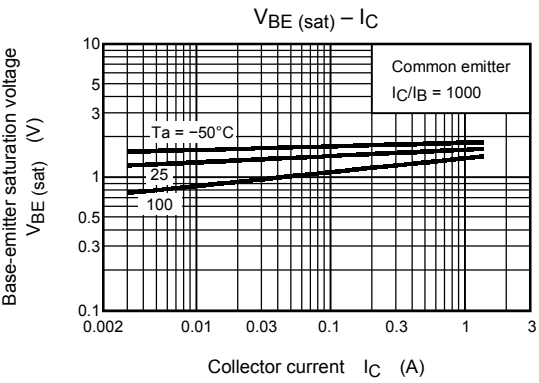
Marking



Explanation of Lot No.







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